

### P-Channel 30-V (D-S) MOSFET

### Description

These miniature surface mount MOSFETs utilize High Cell Density process. Low rDS(on) assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are lower voltage application, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

#### Features

- Low rDS(on) trench technology
- Low thermal impedance
- Fast switching speed
- Low thermal impedance copper lead frame SOT-23 saves board space
- RoHS compliant package

### **Typical Applications**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Package type : SOT-23

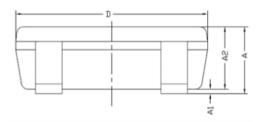
### **Packing & Order Information**

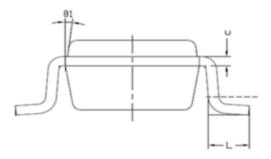
3,000/Reel



Graphic symbol







Symbol	MILLIMETERS			
Symbol	MIN	MAX		
Α	0.8	1.2		
A1	0	0.1		
A2	0.7	1.1		
b	0.3	0.5		
С	0.1			
D	2.7	3.1		
E	2.6	3		
E1	1.4	1.8		
е	0.95 BSC			
e1	1.9 BSC			
L	0.3	0.6		
θ1	7° NOM			

D



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### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)					
Symbol	Parameter	Value	Unit		
V <sub>DS</sub>	Drain-Source Voltage	-30	V		
V <sub>GS</sub>	Gate-Source Voltage	±8	V		
ID	Continuous Drain Current <sup>a</sup> (T <sub>A</sub> =25°C)	-3.9	А		
	Continuous Drain Current <sup>a</sup> (T <sub>A</sub> =70°C)	-3.1	А		
IDM	Pulsed Drain Current <sup>b</sup>	-1.0	А		
Is	Continuous Source Current (Diode Conduction) <sup>a</sup>	-1.7	А		
P <sub>D</sub>	Power Dissipation <sup>a</sup> ( $T_A = 25^{\circ}C$ )	1.3	W		
	Power Dissipation <sup>a</sup> ( $T_A = 70^{\circ}C$ )	0.8	W		
$T_J/T_{STG}$	Operating Junction and Storage Temperature	-55 to +150	°C		

THERMAL RESISTANCE RATINGS					
Symbol	Parameter Maximum				
Reja	Maximum Junction-to-Ambient C/W <sup>a</sup> (t <= 10 sec)	100	°C/W		
	Maximum Junction-to-Ambient C/W <sup>a</sup> (Steady-State)	166	C/ W		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

Electrical Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS},I_{D}\text{=-}250\mu A$	-0.4			v
I <sub>GSS</sub>	Gate-Body Leakage	$V_{DS}=0$ V, $V_{GS}=\pm 8$ V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS}$ = -24 V , $V_{GS}$ = 0 V			-1	uA
		$V_{DS}$ = -24 V , $V_{GS}$ = 0 V , $T_J$ = 55°C			-25	
ID(on)	On-State Drain Current <sup>A</sup>	$V_{DS} = -5 V, V_{Gs} = -4.5 V$	-5			A
<sup>r</sup> DS (on)	Drain-Source On-Resistance <sup>A</sup>	$V_{DS} = -4.5 V$ , $I_{D} = -2.5 A$			57	mΩ
		$V_{DS} = -2.5 V, I_{D} = -2 A$			89	
g <sub>fs</sub>	Forward Tranconductance <sup>A</sup>	$V_{GS} = -15V, I_D = -2.5 A$		10		S
Vsd	Diode Forward Voltage	$I_{\rm S} = -0.9  {\rm A},  V_{\rm GS} = 0  {\rm V}$		-0.8		V



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Dynamic <sup>b</sup>						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
Qg	Total Gate Charge	$V_{DS} = -15 \text{ V}$ , $I_D = -2.5 \text{ A}$ , - $V_{GS} = -4.5 \text{ V}$		12		nC
$Q_{gs}$	Gate-Source Charge			1.9		nC
$Q_{gd}$	Gate-Drain Charge			3.6		nC
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DG} = -15 V, I_D = -2.5 A,$ $V_{GEN} = -4.5 V, R_L = 6 \Omega$ $R_{GEN} = 6 \Omega$		12		ns
tr	Rise Time			9		ns
t <sub>d(off)</sub>	Turn-Off Delay Time			42		ns
tf	Fall Time			15		ns
CISS	Input Capacitance	$V_{DS} = -15 V, V_{GS} = 0 V,$ f = 1.0MHz		684		pF
Coss	Output Capacitance			75		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			60		pF

Notes

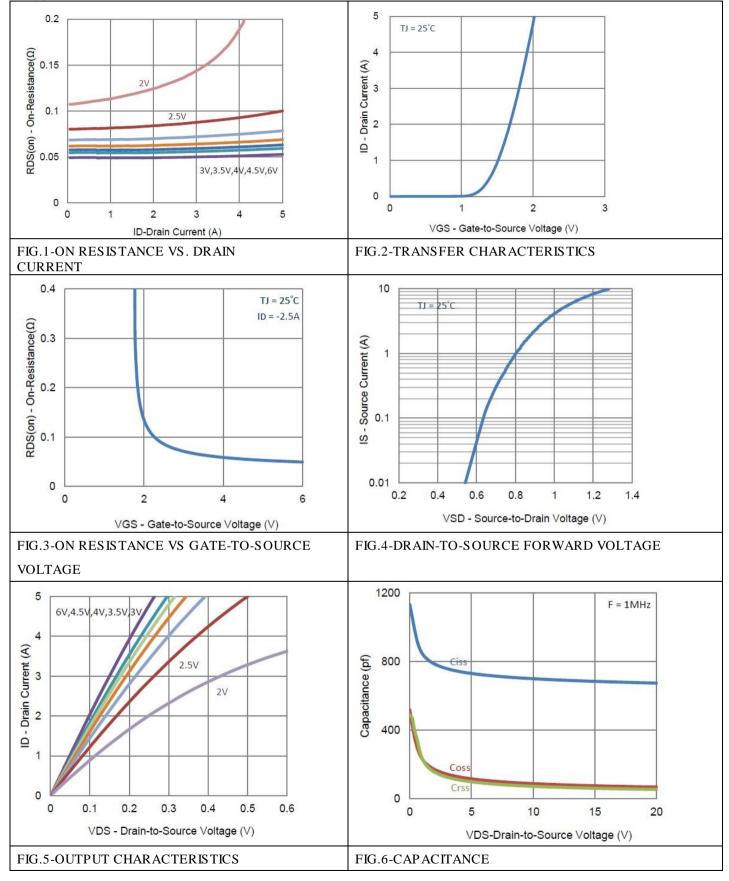
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.



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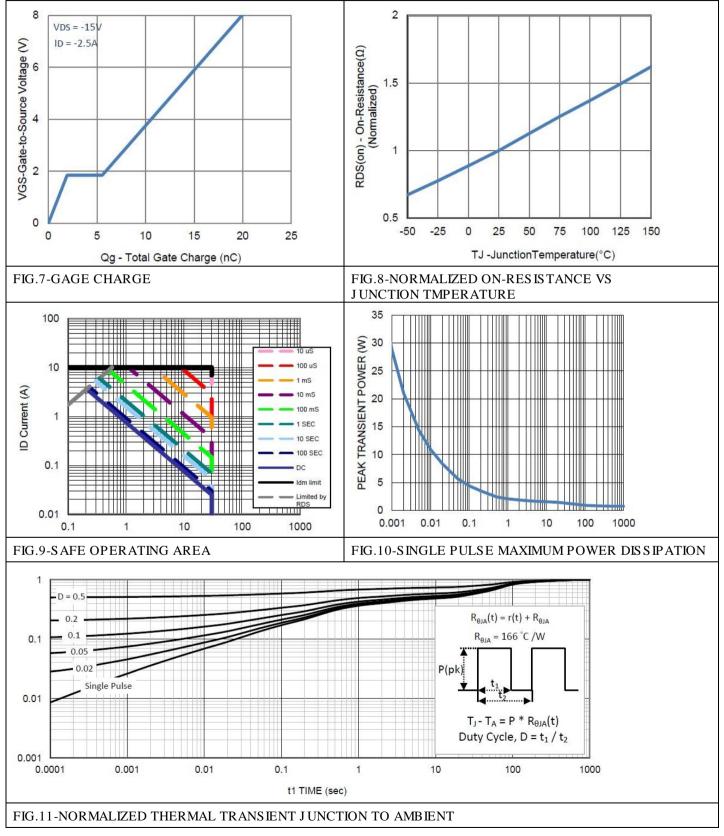
■Typical Electrical Characteristics





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Typical Electrical Characteristics





## MS23P39

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